

**AMENDMENTS TO THE CLAIMS**

Please withdraw Claims 16-20 from consideration without prejudice. Please also add Claims 31 and 32.

Claims 1-15 (Previously cancelled)

Claims 16-20 (Cancelled)

21. (AMENDED) A method of fabricating a semiconductor device having a semiconductor region, the method comprising the steps of:

forming at least two conductive posts overlying the semiconductor region to form a structure;

encapsulating the structure and at least one of the at least two conductive posts to form a planarized cured passivation layer; and

exposing the at least one of the at least two conductive posts through the planarized cured passivation layer to form the semiconductor device, wherein the step of forming at least two conductive posts comprises a lift-off step.

22. (AMENDED) The method of Claim 21, wherein ~~the step of forming at least two conductive posts comprises a lift off step, and~~ at least one of the at least ~~one~~ two conductive posts comprises at least one of Pt, Au and Ti.